SN74LVC2G125 DUAL BUS BUFFER GATE WITH 3-STATE OUTPUTS

SCES204I - APRIL 1999 - REVISED JANUARY 2003

- Available in the Texas Instruments NanoStar[™] and NanoFree[™] Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 4.3 ns at 3.3 V
- Low Power Consumption, 10-μA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce)
 <0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 >2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
 - ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

description/ordering information

This dual bus buffer gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G125 features dual line drivers with 3-state outputs. The outputs are disabled when the associated output-enable (\overline{OE}) input is high.

NanoStar[™] and NanoFree[™] package technology is a major breakthrough in IC packaging concepts, using the die as the package.

ORDERING INFORMATION

TA	PACKAGET		ORDERABLE PART NUMBER	TOP-SIDE MARKING‡	
–40°C to 85°C	NanoStar™ WCSP (DSBGA) – YEA	Reel of 3000	SN74LVC2G125YEAR	CM_	
	NanoFree™ WCSP (DSBGA) – YZA (Pb-free)	Reel of 3000	SN74LVC2G125YZAR		
	SSOP – DCT	Reel of 3000	SN74LVC2G125DCTR	C25	
	VSSOP – DCU	Reel of 3000	SN74LVC2G125DCUR	005	
		Reel of 250	SN74LVC2G125DCUT	025_	

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site. DCU: The actual top-side marking has one additional character that designates the assembly/test site. YEA/YZA: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site.



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DCT OR DCU PACKAGE (TOP VIEW)									
10E [1	0	8] V <u>cc</u>					
1A [2		7] 20E					
2Y [3		6] 1Y					
GND [4		5] 2A					

YEA OR YZA PACKAGE (BOTTOM VIEW)

GND	04	50	2A
2Y	Ο3	60	1Y
1A	02	70	2 <mark>OE</mark>
1 <mark>OE</mark>	01	80	v_{CC}

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description/ordering information (continued)

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

FUNCTION TABLE (each buffer)								
INPUTS OUTPUT								
OE	Α	Y						
L	Н	Н						
L	L	L						
н	Х	Z						

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC} Input voltage range, V _I (see Note 1)	0.5 V to 6.5 V 0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V _O	
(See Note 1)	–0.5 V to 6.5 V
voltage range applied to any output in the high or low state, vo	
(see Notes 1 and 2)	–0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I_{OK} (V _O < 0)	–50 mA
Continuous output current, I _O	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DCT package	220°C/W
DCU package	227°C/W
YEA/YZA package	140°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The value of V_{CC} is provided in the recommended operating conditions table.
 - 3. The package thermal impedance is calculated in accordance with JESD 51-7.



recommended operating conditions (see Note 4)

			MIN	MAX	UNIT				
	Supply voltage	Operating	1.65	5.5	V				
VCC	Supply voltage	Data retention only	1.5		V				
		V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$						
Maria	High-level input voltage	V _{CC} = 2.3 V to 2.7 V	1.7		Ň				
I VIH		$V_{CC} = 3 V \text{ to } 3.6 V$	2		V				
		V_{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$						
		V _{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$					
Ma	Low-level input voltage $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	V _{CC} = 2.3 V to 2.7 V		0.7					
VIL		$V_{CC} = 3 V \text{ to } 3.6 V$		0.8	V				
		$V_{CC} = 4.5 V \text{ to } 5.5 V$		$0.3 \times V_{CC}$					
VI	Input voltage		0	5.5	V				
٧ ₀	Output voltogo	High or low state	0	VCC	V				
	3-state	0	5.5	v					
		V _{CC} = 1.65 V		-4					
	High-level output current	V _{CC} = 2.3 V		-8					
ЮН				-16	mA				
		vCC = 3 v		-24					
		V _{CC} = 4.5 V		-32					
		V _{CC} = 1.65 V		4					
		V _{CC} = 2.3 V		8					
IOL	Low-level output current			16	mA				
		$v_{CC} = 3 v$		24					
		V _{CC} = 4.5 V		32					
		V_{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20					
$\Delta t/\Delta v$	Input transition rise or fall rate	$V_{CC} = 3.3 V \pm 0.3 V$		10	ns/V				
		$V_{CC} = 5 V \pm 0.5 V$							
ТА	Operating free-air temperature		-40	85	°C				

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	Vcc	MIN	TYP†	MAX	UNIT	
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} -0.1				
	I _{OH} = -4 mA	1.65 V	1.2				
Maria	I _{OH} = -8 mA	2.3 V	1.9				
∨он	I _{OH} = -16 mA	2.1/	2.4			v	
	I _{OH} = -24 mA	3 V	2.3				
V _{OH} V _{OL} I _I A or OE inputs I _{off} I _{OZ}	I _{OH} = -32 mA	4.5 V	3.8				
	I _{OL} = 100 μA	1.65 V to 5.5 V			0.1		
	I _{OL} = 4 mA	1.65 V			0.45		
	I _{OL} = 8 mA	2.3 V			0.3	V	
VOL	I _{OL} = 16 mA	2.1			0.4	v	
	I _{OL} = 24 mA	3 V			0.55		
	I _{OL} = 32 mA	4.5 V			0.55		
I A or OE inputs	$V_I = 5.5 V \text{ or GND}$	0 to 5.5 V			±5	μA	
l _{off}	$V_{I} \text{ or } V_{O} = 5.5 \text{ V}$	0			±10	μA	
I _{OZ}	$V_{O} = 0$ to 5.5 V	3.6 V			10	μΑ	
ICC	$V_{I} = 5.5 V \text{ or GND}, \qquad I_{O} = 0$	1.65 V to 5.5 V			10	μΑ	
ΔICC	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V			500	μΑ	
Data inputs		2.2.1/		3.5		ъĘ	
Control inputs		3.3 V 4					
Co	$V_{O} = V_{CC} \text{ or } GND$	3.3 V		6.5		pF	

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

PARAMETER			V _{CC} = ± 0.1	1.8 V 5 V	= ۷ _{CC} ± 0.2	2.5 V 2 V	= V _{CC} ± 0.3	3.3 V 3 V	: V _{CC} ± 0	= 5 V 5 V	UNIT
		(001101)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
^t pd	A	Y	3.3	9.1	1.5	4.8	1.4	4.3	1	3.7	ns
t _{en}	OE	Y	4	9.9	1.9	5.6	1.2	4.7	1.2	3.8	ns
^t dis	OE	Y	1.5	11.6	1	5.8	1.4	4.6	1	3.4	ns

operating characteristics, T_{A} = 25 $^{\circ}$

PARAMETER		TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V		
		CONDITIONS	TYP	TYP	TYP	ТҮР		
C _{pd}	Power dissipation	Outputs enabled	f - 10 MH-	19	19	20	22	ъĘ
	capacitance	Outputs disabled		2	2	2	3	рг



PARAMETER MEASUREMENT INFORMATION



- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{O} = 50 $\Omega.$
- D. The outputs are measured one at a time with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.
- H. All parameters and waveforms are not applicable to all devices.





MPDS049B - MAY 1999 - REVISED OCTOBER 2002

DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion

D. Falls within JEDEC MO-187 variation DA.



MPDS050B - FEBRUARY 2000 - REVISED OCTOBER 2002

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187



MXBG002B AUGUST 2001 - REVISED MAY 2002



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar package configuration.
- D. Package complies to JEDEC MO-211 variation EB.
- E. This package is tin-lead (SnPb). Refer to the 8 YZA package (drawing 4204151) for lead-free.



MXBG006A - JANUARY 2002 - REVISED APRIL 2002



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoFree[™] package configuration.
- D. Package complies to JEDEC MO-211 variation EB.
- E. This package is lead-free. Refer to the 8 YEA package (drawing 4203167) for tin-lead (SnPb).

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